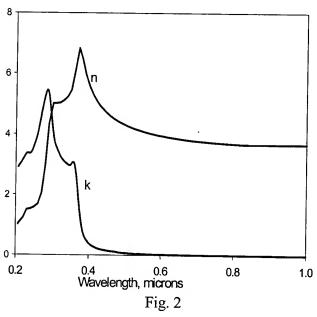


Fig. 1 (PRIOR ART)



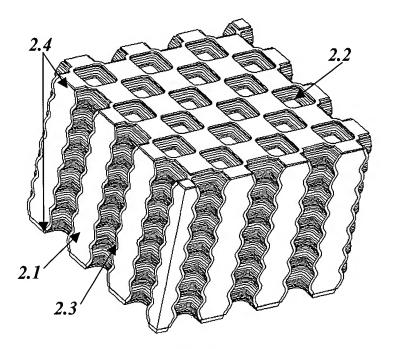


Fig. 3a

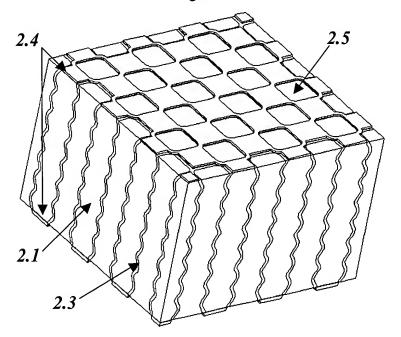


Fig. 3b

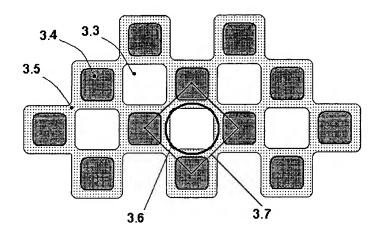


Fig. 4a

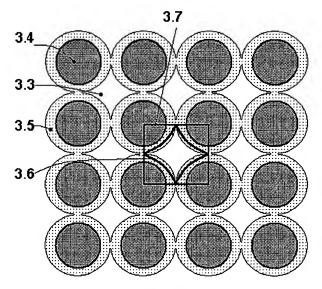


Fig. 4b

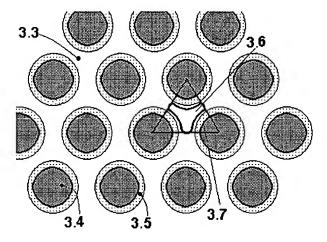


Fig. 4c

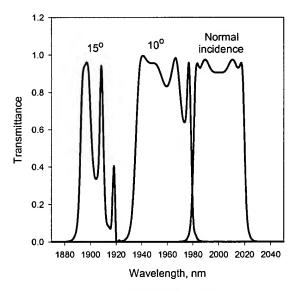


Fig. 5a (PRIOR ART)

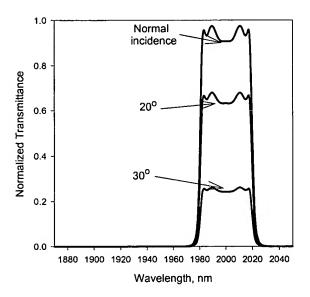


Fig. 5b

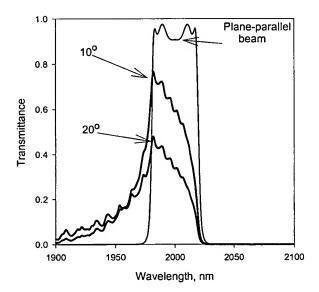


Fig. 5c (PRIOR ART)

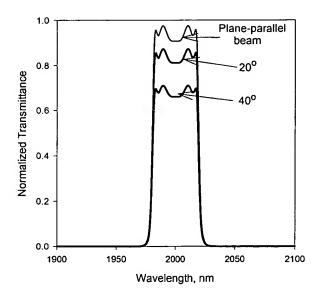


Fig. 5d

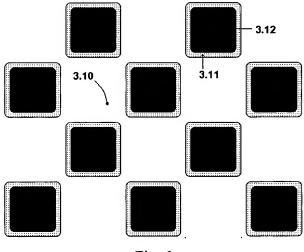


Fig. 6

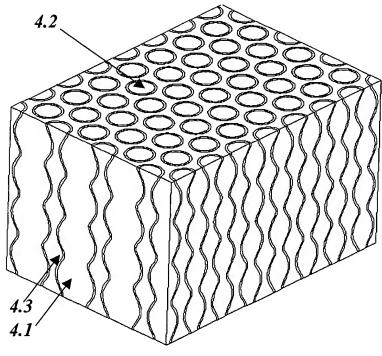


Fig. 7

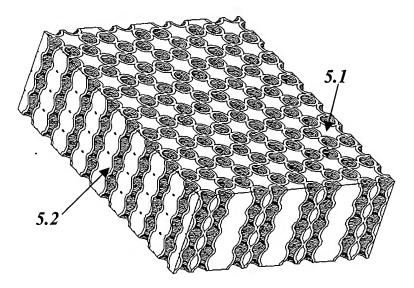


Fig. 8a

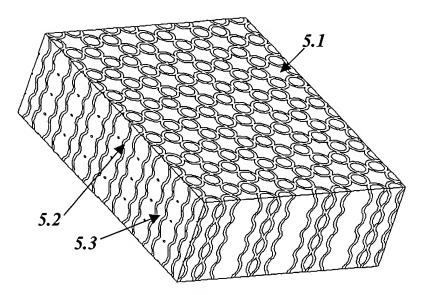


Fig. 8b

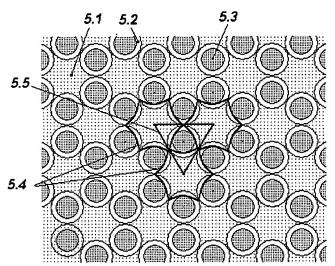


Fig. 8c

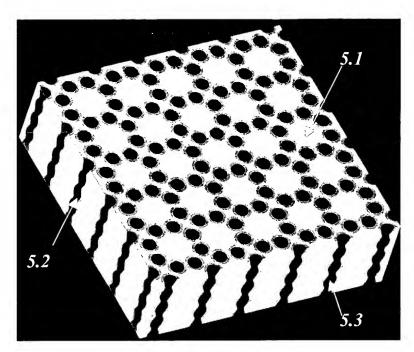


Fig. 9a

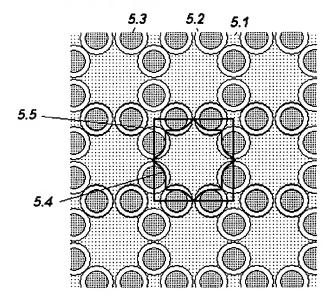
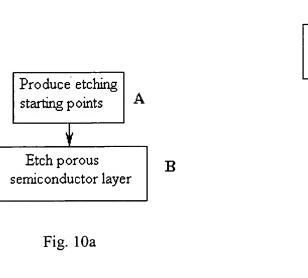
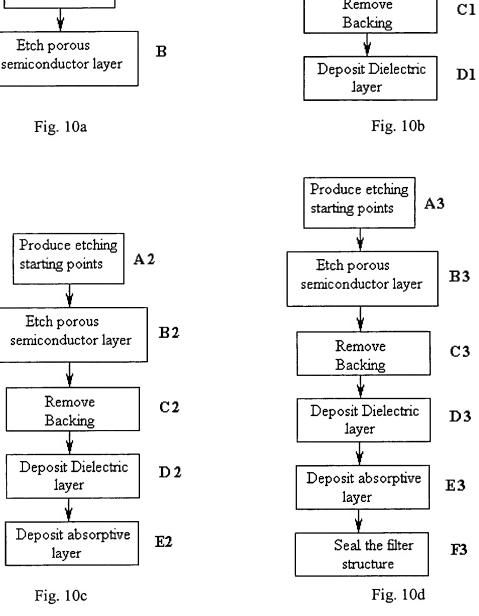


Fig. 9b





Produce etching

starting points

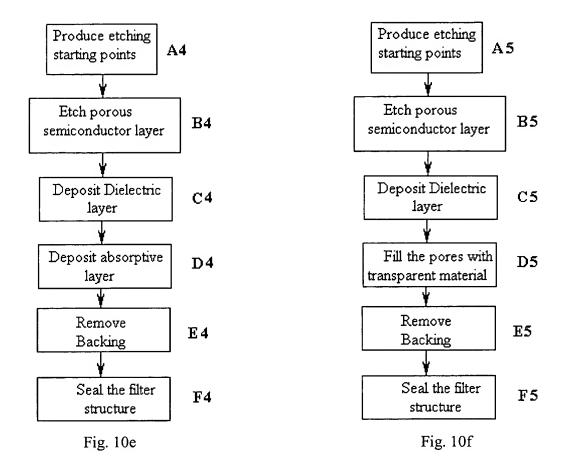
Etch porous

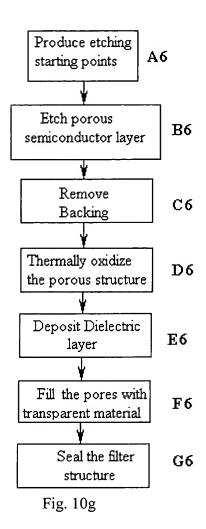
semiconductor layer

Remove

Al

B1





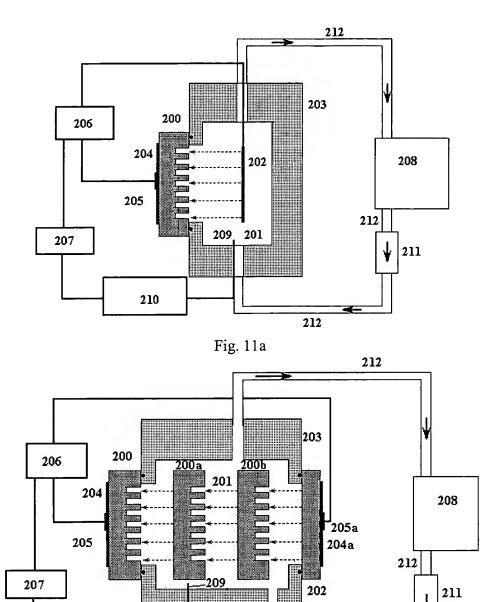


Fig. 11b

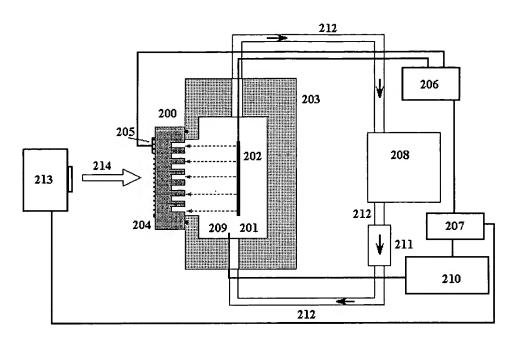


Fig. 11c

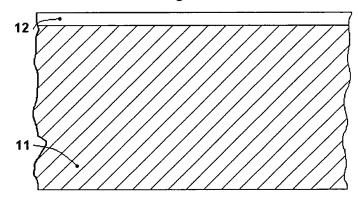
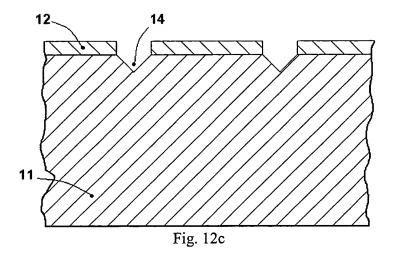


Fig. 12a

Fig. 12b



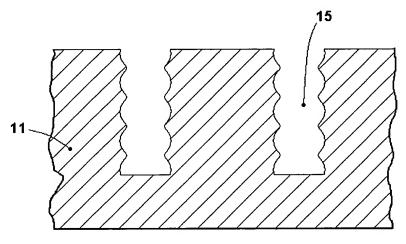


Fig. 12d

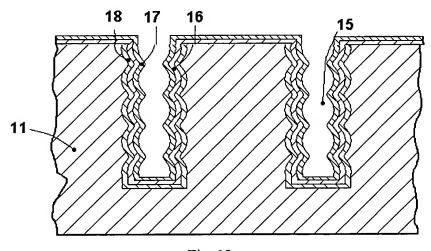


Fig. 12e

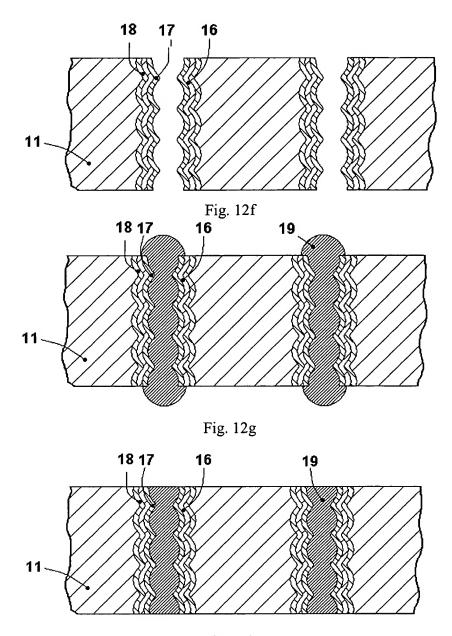


Fig. 12h

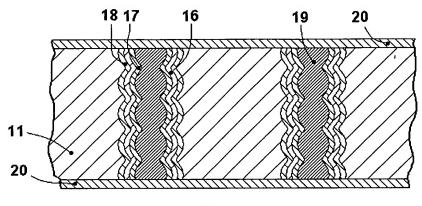


Fig. 12i

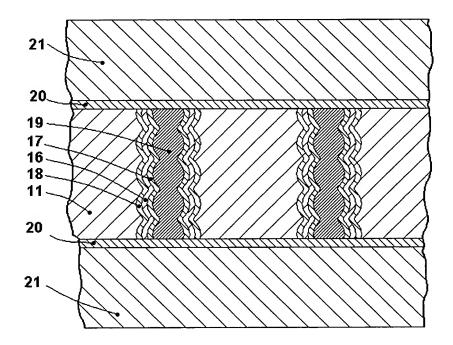


Fig. 12j

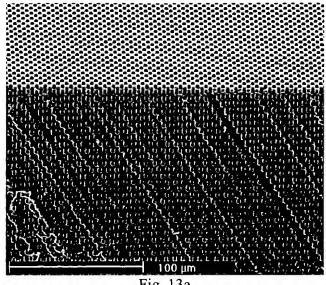


Fig. 13a

Fig. 13b

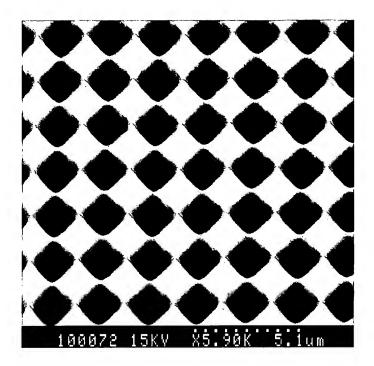


Fig. 13c

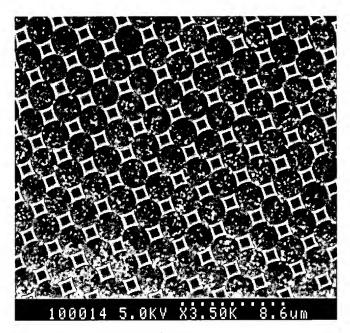


Fig. 14a

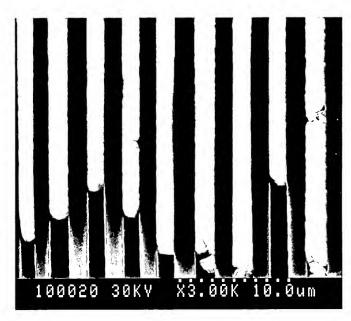


Fig. 14b

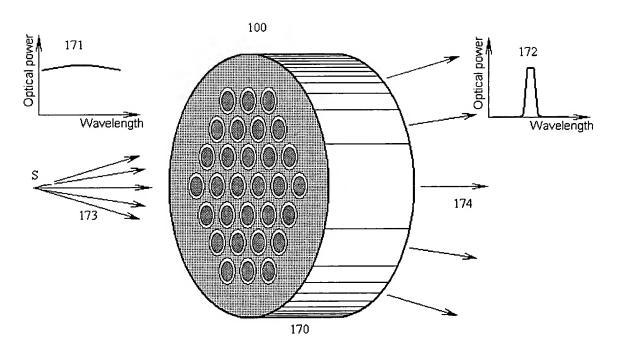


Fig. 15